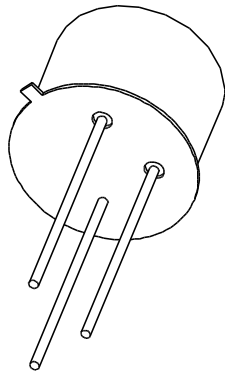


# DATA SHEET



## **BSX45; BSX46; BSX47** NPN medium power transistors

Product specification  
Supersedes data of September 1994  
File under Discrete Semiconductors, SC04

1997 Apr 23

**NPN medium power transistors**

**BSX45; BSX46; BSX47**

**FEATURES**

- High current (max. 1 A)
- Low voltage (max. 80 V).

**APPLICATIONS**

- General industrial applications.

**DESCRIPTION**

NPN medium power transistor in a TO-39 metal package.

**PINNING**

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case

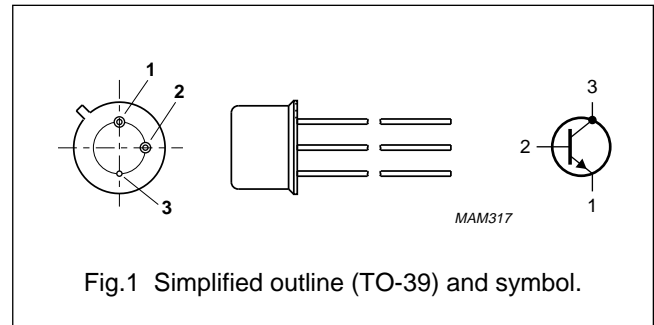


Fig.1 Simplified outline (TO-39) and symbol.

**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter				
	BSX45		–	–	80	V
	BSX46		–	–	100	V
V <sub>CEO</sub>	collector-emitter voltage	open base				
	BSX45		–	–	40	V
	BSX46		–	–	60	V
	BSX47		–	–	80	V
I <sub>CM</sub>	peak collector current		–	–	1.5	A
P <sub>tot</sub>	total power dissipation	T <sub>case</sub> ≤ 25 °C	–	–	6.25	W
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 100 mA; V <sub>CE</sub> = 1 V				
	BSX45-10; BSX46-10; BSX47-10		63	100	160	
	BSX45-16; BSX46-16; BSX47-16		100	160	250	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 50 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	50	–	–	MHz

## NPN medium power transistors

## BSX45; BSX46; BSX47

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSX45		–	80	V
	BSX46		–	100	V
	BSX47		–	120	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BSX45		–	40	V
	BSX46		–	60	V
	BSX47		–	80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	7	V
I <sub>C</sub>	collector current (DC)		–	1	A
I <sub>CM</sub>	peak collector current		–	1.5	A
I <sub>BM</sub>	peak base current		–	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>case</sub> ≤ 25 °C	–	6.25	W
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	200	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air	200	K/W
R <sub>th j-c</sub>	thermal resistance from junction to case		28	K/W

## NPN medium power transistors

## BSX45; BSX46; BSX47

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current BSX45; BSX46	$I_E = 0; V_{CB} = 60\text{ V}$	–	–	30	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 150\text{ }^{\circ}\text{C}$	–	–	10	$\mu\text{A}$
$I_{CBO}$	collector cut-off current BSX47	$I_E = 0; V_{CB} = 80\text{ V}$	–	–	30	nA
		$I_E = 0; V_{CB} = 80\text{ V}; T_{amb} = 150\text{ }^{\circ}$	–	–	10	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	10	nA
$h_{FE}$	DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 1\text{ V}$	15	40	–	
			25	90	–	
$h_{FE}$	DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16; BSX47-16	$I_C = 100\text{ mA}; V_{CE} = 1\text{ V}$	63	100	160	
			100	160	250	
$h_{FE}$	DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16	$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	25	40	–	
			35	60	–	
$h_{FE}$	DC current gain BSX45-10; BSX46-10; BSX47-10 BSX45-16; BSX46-16	$I_C = 1\text{ A}; V_{CE} = 1\text{ V}$	–	20	–	
			–	30	–	
$V_{CEsat}$	collector-emitter saturation voltage BSX45; BSX46	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	1	V
$V_{CEsat}$	collector-emitter saturation voltage BSX47	$I_C = 500\text{ mA}; I_B = 25\text{ mA}$	–	–	900	mV
$V_{BE}$	base-emitter voltage	$I_C = 100\text{ mA}; V_{CE} = 1\text{ V}$	–	–	1	V
		$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	0.75	–	1.5	V
		$I_C = 1\text{ A}; V_{CE} = 1\text{ V}$	–	–	2	V
$C_c$	collector capacitance BSX45 BSX46 BSX47	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	25	pF
			–	–	20	pF
			–	–	15	pF
$C_e$	emitter capacitance	$I_C = I_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	–	80	pF
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	50	–	–	MHz
F	noise figure	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 1\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	3.5	–	dB
<b>Switching times (between 10% and 90% levels)</b>						
$t_{on}$	turn-on time	$I_{Con} = 100\text{ mA}; I_{Bon} = 5\text{ mA};$ $I_{Boff} = -5\text{ mA}$	–	–	200	ns
$t_{off}$	turn-off time		–	–	850	ns

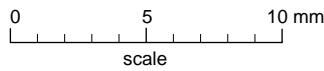
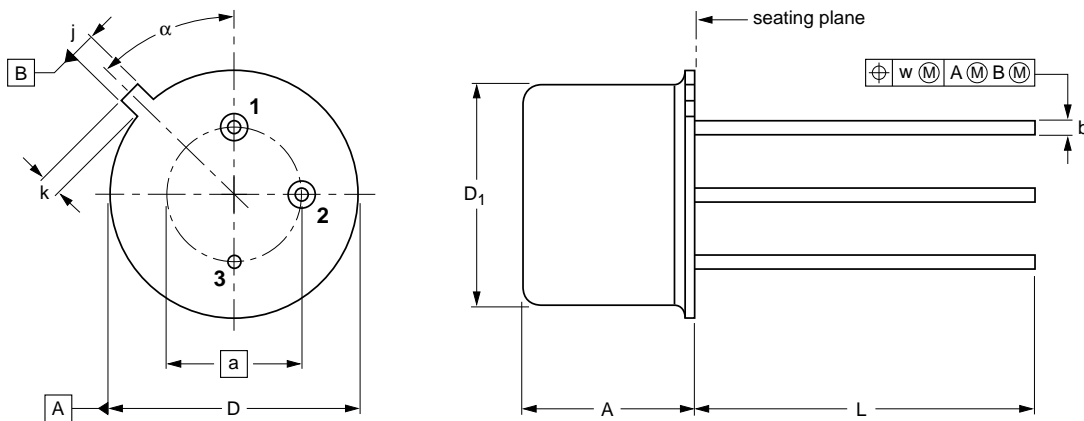
NPN medium power transistors

BSX45; BSX46; BSX47

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D <sub>1</sub>	j	k	L	w	α
mm	6.60	0.48	9.39	8.33	0.85	0.95	14.2	0.2	45°	
	6.35	5.08	0.41	9.08	8.18	0.75	12.7			

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

## NPN medium power transistors

## BSX45; BSX46; BSX47

**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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NPN medium power transistors

BSX45; BSX46; BSX47

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